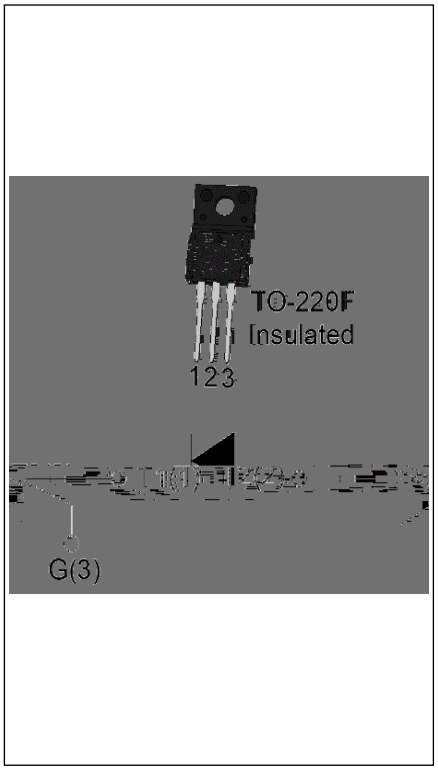
JST16F-800B 16A TRIAC

Rev.A.1.1

The JST16F-800B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an external plastic package, JST16F-800B provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM} /V_{RRM}	800	V
I_{GT} / / /	50/50/50/70	mA

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	
Operating junction temperature range		T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)		V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25)		V_{RRM}	800	V
RMS on-state current ($T_C \leq$ 73)		$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle , t_p=20ms , T_j=25)		I_{TSM}	160	A
Non repetitive surge peak on-state current (full cycle , t_p=16.6ms , T_j=25)			176	
I^2t value for fusing (t_p=10ms , T_j=25)		I^2t	128	A^2s
Critical rate of rise of on-state current (I_G=2 × I_{GT} , f=100Hz , T_j=125)	-	dI/dt	100	A/μs
	-		50	
Peak gate current (t_p=20μs , T_j=125)		I_{GM}	4	A
Average gate power dissipation (T_j=125)		$P_{G(AV)}$	0.5	W

Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D=12V R_L=33Ω	- -	MAX.	50	mA
				70	
V_{GT}		ALL	MAX.	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	ALL	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	- -	MAX.	70	mA
				100	
I_H	I_T=500mA		MAX.	60	mA
dV/dt	V_D=540V Gate Open T_j=125		MIN.	1000	V/μs
(dV/dt)c	(dI/dt)c=7A/ms, T_j=125		MIN.	12	V/μs
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	5	μs
t_{off}				50	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM}=22.5A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.77	V
R_D	Dynamic resistance	T_j=125	30	mΩ
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=125	0.5	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.3	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

FIG.1: Maximum power dissipation versus RMS on-state current

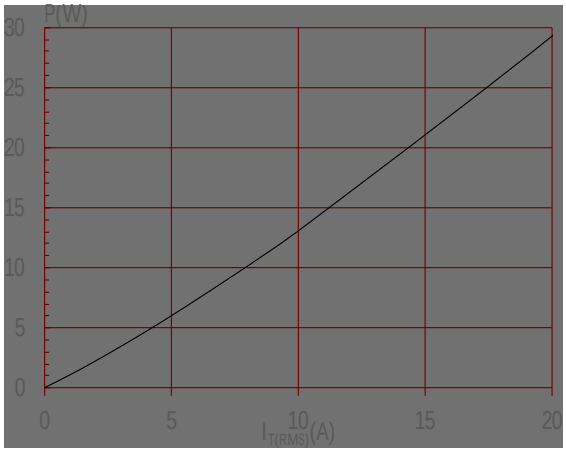


FIG.2: RMS on-state current versus case temperature

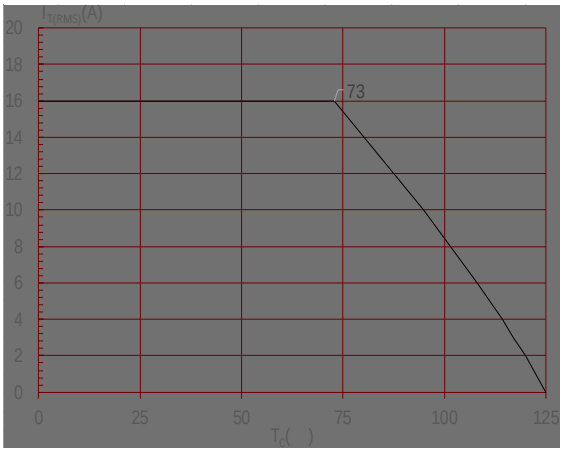


FIG.3: Surge peak on-state current versus number of cycles

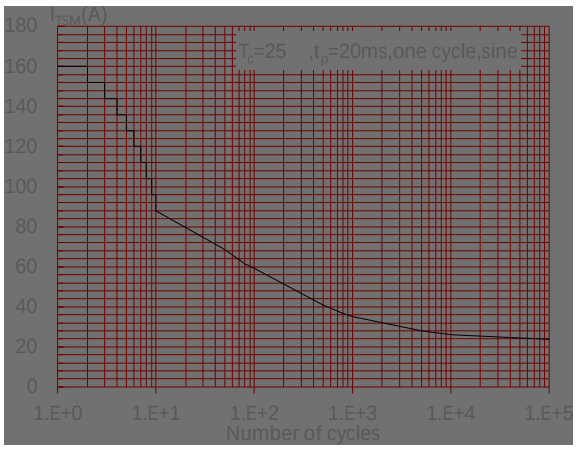
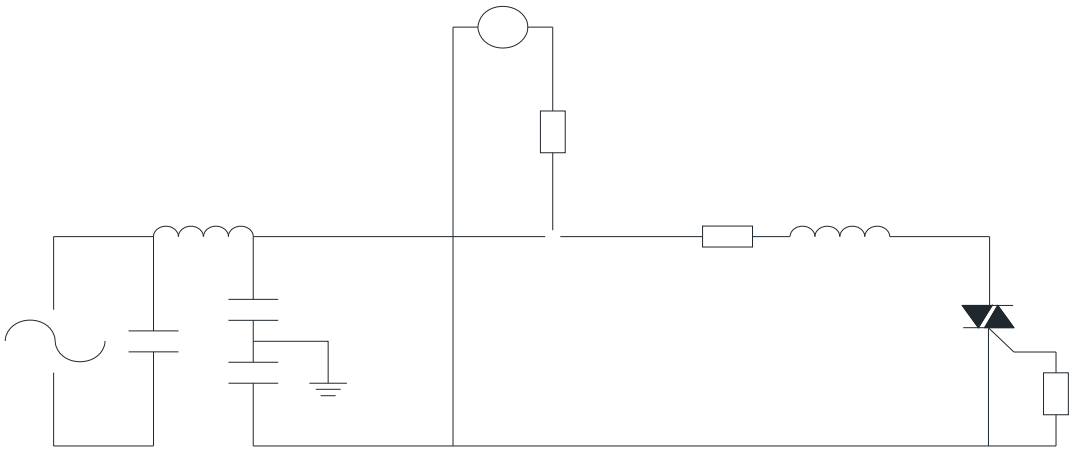


FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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